IN THE CLAIMS:

Listing of claims:

1. (previously presented) A method for forming a head suspension assembly, comprising:

forming a trench extending into a substrate;

forming a sacrificial layer in the trench;

forming a film across the substrate;

patterning a photoresist layer on top of the film;

transferring an image of the patterned photoresist layer through the film;

removing the patterned photoresist layer; and

removing the sacrificial layer from the trench to form a cavity extending a distance into the substrate.

- 2. (previously presented) A method as in claim 1, wherein the film includes silicon.
- 3. (previously presented) A method as in claim 1, wherein the transferring the image of the patterned photoresist layer through the film is done using reactive ion etching.
- 4. (original) A method as in claim 1, wherein the substrate comprises silicon and the sacrificial layer is formed by etching a trench in the substrate and filling the trench with a metal.
- 5. (original) A method as in claim 4, wherein removing the sacrificial layer comprises etching the metal from the trench.
- 6. (previously presented) A method as in claim 1, further comprising forming the film from a polymer material.

7. (previously presented)	A method as in claim 1, wherein the substrate comprises
silicon and the film comprises polys	silsesquioxone.
8. (previously presented)	A method as in claim 1, wherein the cavity extends a width
that is no greater than that of the sul	bstrate and the cavity extends a depth that is less than a depth
of the substrate.	
9. (previously presented)	A method as in claim 1, further comprising forming an
adhesion layer between the substrat	e and the film.
10. (previously presented)	A method as in claim 3, wherein the film comprises a resin,
	after the removing the sacrificial layer.
11. (canceled)	
12. (currently amended)	A method as in claim 13 11, further comprising, prior to
forming the photoresist layer, curing	g the polysilsesquioxone layer.
13. (currently amended)	A method as in claim 11, further comprising, for forming a
head suspension assembly, compris	
	e layer over a portion of a substrate;
	on the polysilsesquioxone layer;
patterning the photoresist la	
	ne layer using the patterned photoresist layer as a mask;
removing the patterned phot	
	esquioxone layer, forming a trench in the substrate and
	nch, wherein the polysilsesquioxone layer is formed over the
sacrificial layer.	
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- 14. (original) A method as in claim 13, further comprising forming the sacrificial layer from a metal material.
- 15. (original) A method as in claim 13, further comprising forming the sacrificial layer from copper.
- 16. (original) A method as in claim 13, further comprising removing the sacrificial material from the trench after the etching the polysilsesquioxone layer.
- 17. (currently amended) A method as in claim 13, 12, further comprising positioning a slider on the cured polysilsesquioxone layer after the removing the patterned photoresist layer.

18-20. (canceled)